

CLAIMS

What is claimed is:

- 1 1. An apparatus for closing a chamber, the chamber having a first chamber housing and a
2 second chamber housing, comprising:
3 means for forming a chamber including means for bringing the first chamber
4 housing into contact with the second chamber housing; and
5 deforming means for preventing formation of particles while the first chamber
6 housing contacts the second chamber housing, wherein the deforming means is mounted
7 on at least one of the first chamber housing and the second chamber housing such that it
8 deforms to accommodate any misalignment while the means for forming a chamber
9 operates.
- 1 2. The apparatus of claim 1 wherein the first chamber housing includes a first interior
2 surface defining a first cavity.
- 1 3. The apparatus of claim 2 wherein the first interior surface defining a first cavity is sized
2 to contain a semiconductor wafer for forming integrated circuits.
- 1 4. The apparatus of claim 2 wherein the second chamber housing includes a second interior
2 surface defining a second cavity.
- 1 5. The apparatus of claim 4 wherein the second interior surface defining a second cavity is
2 sized such that when juxtaposed with the first cavity a region thereby formed is
3 sufficiently sized to contain a semiconductor wafer for forming integrated circuits.
- 1 6. The apparatus of claim 1 wherein the first chamber housing is mounted to a structure for
2 stabilizing the first chamber housing while the first chamber housing contacts the second
3 chamber housing.

- 1 7. The apparatus of claim 6 wherein the second chamber housing is driven by a motivating
2 structure, being constructed and arranged to move the second chamber housing in and out
3 of contact with the first chamber housing.

- 1 8. The apparatus of claim 7 wherein the motivating structure is powered by at least one of a
2 pneumatic source, a hydraulic source, a turbine, and a motor.

- 1 9. The apparatus of claim 7 wherein the motivating structure comprises:
2 a body defining a casing; and
3 a moveable member, being positioned in the casing and being reciprocable along
4 an axis between a first position and a second position, wherein the second chamber
5 housing contacts the first chamber housing while the moveable member is in the first
6 position, and wherein the second chamber housing is not in contact with the first chamber
7 housing while the moveable member is in the second position.

- 1 10. The apparatus of claim 9 wherein the deforming means comprises at least one of a
2 material between a surface of the first chamber housing and a surface of the structure to
3 which the first chamber housing is mounted, a material between a surface of the second
4 chamber housing and a surface of the motivating structure, and a material between a
5 surface of the moveable member and a surface of the casing.

- 1 11. The apparatus of claim 10 wherein the material comprises an abrasion resistant material
2 characterized by high impact strength and having a low coefficient of friction.

- 1 12. The apparatus of claim 10 wherein the material comprises at least one of polyether ether
2 ketone (PEEK™), thermoplastic resin, polyolefin type resin, polyamide resin, polyester
3 resin, polyether resin, polynitrile resin, polymethacrylate resin, polyvinyl resin, cellulose
4 resin, fluorine resin and a composition of PEEK™ and at least one of resins and fillers.

- 1 13. The apparatus of claim 1 further comprising alignment means for reducing an amplitude
2 of relative motion between the first chamber housing and the second chamber housing
3 while the first chamber housing contacts the second chamber housing.

- 1 14. The apparatus of claim 13 wherein the alignment means comprises a first chamber
2 housing feature adapted to engage with a second chamber housing feature to particularly
3 position the second chamber while the first chamber housing contacts the second chamber
4 housing.
- 1 15. The apparatus of claim 14 wherein at least one of the first chamber housing feature and
2 the second chamber housing feature comprises a protrudance, wherein the protrudance
3 has a particularly shaped outer edge adapted to interfit with a recess defined in at least
4 one of the first chamber housing and the second chamber housing.
- 1 16. The apparatus of claim 13 wherein the alignment means comprises a pin-like structure
2 located on at least one of the first chamber housing and the second chamber housing and
3 an aperture defined in at least one of the first chamber housing and the second chamber
4 housing to securely receive the pin-like structure.
- 1 17. The apparatus of claim 16 wherein the aperture is elongated in shape and has at least one
2 chamfered inner wall adapted to facilitate alignment of the aperture with the pin-like
3 structure.
- 1 18. The apparatus of claim 1 wherein at least one of the first chamber housing and the second
2 chamber housing comprises a manifold having thereon a plurality of fluid outlets for
3 distributing a process fluid.
- 1 19. The apparatus of claim 1 further comprising means for performing a supercritical process.
- 1 20. The apparatus of claim 19 wherein the means for performing a supercritical process
2 comprises means for circulating at least one of gaseous, liquid, supercritical and near-
3 supercritical carbon dioxide in the chamber.

- 1 21. A method of closing a chamber, the chamber having a first chamber housing and a second
2 chamber housing, comprising the steps of:
- 3 a. forming a chamber including bringing the first chamber housing into contact with
4 the second chamber housing; and
- 5 b. preventing formation of particles while the first chamber housing contacts the
6 second chamber housing.
- 1 22. The method of claim 21 wherein the step of forming a chamber comprises moving the
2 second chamber housing in and out of contact with the first chamber housing.
- 1 23. The method of claim 21 wherein the step of preventing formation of particles comprises
2 positioning a material on at least one of the first chamber housing and the second
3 chamber housing such that the material deforms to accommodate any misalignment while
4 forming a chamber.
- 1 24. The method of claim 23 wherein the material comprises an abrasion resistant material
2 characterized by high impact strength and having a low coefficient of friction.
- 1 25. The method of claim 23 wherein the material comprises at least one of polyether ether
2 ketone (PEEK™), thermoplastic resin, polyolefin type resin, polyamide resin, polyester
3 resin, polyether resin, polynitrile resin, polymethacrylate resin, polyvinyl resin, cellulose
4 resin, fluorine resin and a composition of PEEK™ and at least one of resins and fillers.
- 1 26. The method of claim 21 wherein the step of preventing formation of particles comprises
2 configuring an alignment means for reducing an amplitude of relative motion between the
3 first chamber housing and the second chamber housing while the first chamber housing
4 contacts the second chamber housing.
- 1 27. The method of claim 26 wherein the step of employing an alignment means comprises
2 configuring a first-chamber-housing feature to engage with a second-chamber-housing
3 feature to particularly position the second chamber while the first chamber housing
4 contacts the second chamber housing.

- 1 28. The method of claim 21 further comprising processing an object with a fluid.
- 1 29. The method of claim 28 wherein the step of processing an object with a fluid comprises
2 processing a semiconductor wafer with at least one of gaseous, liquid, supercritical and
3 near-supercritical carbon dioxide.
- 1 30. A method of eliminating particle generation at a platen/injection ring interface,
2 comprising the steps of:
3 a. forming a platen/injection ring interface including bringing a platen into contact
4 with an injection ring; and
5 b. positioning a material on at least one of the injection ring and the platen such that
6 the material deforms to accommodate any misalignment while forming the
7 platen/injection ring interface.
- 1 31. A method of 30 further comprising the step of configuring an alignment means for
2 reducing an amplitude of relative motion between the platen and the injection ring while
3 the platen contacts the injection ring.
- 1 32. The method of claim 30 further comprising the step of processing a semiconductor wafer
2 with at least one of gaseous, liquid, supercritical and near-supercritical carbon dioxide.